

Question No 1

Solution: -

$$I_B = 40 \mu A$$

And, given in figure

$$V_{CE} = 4V$$

$$a) \beta_{dc} = \frac{I_C}{I_B}$$

We have to find $I_C = \frac{V_{CC}}{R_C}$
but $I_C = I_E = 4mA$

$$\beta_{dc} = \frac{4mA}{40 \mu A}$$

$$\beta_{dc} = 0.1 \times 10^3$$

$$\beta_{dc} = 100$$

$$b) \alpha_{dc} = \frac{I_C}{I_E} = \frac{4mA}{\frac{20}{4mA}} = 0.99$$

$$c) \boxed{I_E = 0.004 A}$$

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Question No 2

$$R_B = 45 \text{ K}\Omega$$

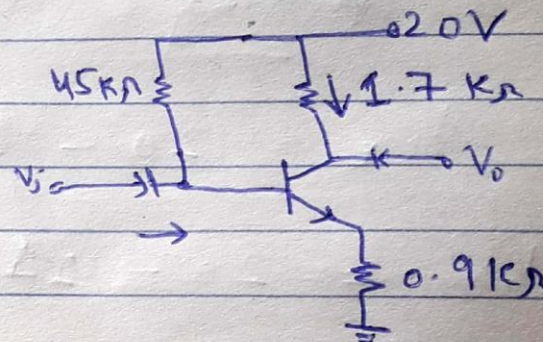
$$R_C = 1.7 \text{ K}\Omega$$

$$R_E = 0.9 \text{ K}\Omega$$

$$\beta = 140$$

a) $I_B = ?$

We know that



$$I_B = \frac{V_{CC} - V_{BE}}{R_B + (\beta + 1)R_E}$$

$$R_B + (\beta + 1)R_E$$

putting values

$$I = \frac{20 - 0.7}{45\text{K} + (140 + 1)(0.9\text{K})}$$

$$I_B = \frac{19.3}{171900}$$

$$I_B = 112.4 \mu\text{A}$$

$$b) I_c = \beta I_B$$

$$I_c = (120) (112.4 \mu A)$$

$$\boxed{I_c = 0.0135 A}$$

$$c) V_{CE} = V_{CC} - I_c (R_c + R_E)$$

Putting values

$$V_{CE} = 20 - 112.4 \mu A (1.7 k\Omega + 0.9 k\Omega)$$

$$V_{CE} = 20 - 112.4 \mu A (2600)$$

$$V_{CE} = 20 - 0.296$$

$$\boxed{V_{CE} = 19.7 V}$$

$$d) V_c = V_{CC} - I_c R_c$$

$$= 20 - 112.4 \mu A (1.7 k)$$

$$= 20 - 0.293$$

$$\boxed{V_c = 19.7}$$

$$e) V_E = I_E R_E$$

$$V_E = I_c R_E$$

$$\therefore I_c \approx I_E$$

$$V_E = 112.4 \mu A (0.9 k)$$

$$\boxed{V_E = 0.100 V}$$

Question No 3

$$R_B = 0 \Omega$$

$$R_C = 2 \Omega$$

$$R_E = 3 \Omega$$

$$a) r_e = \frac{26 \text{ mV}}{I_E}$$

we first find I_E

$$I_E = (\beta + 1) I_B$$

$$I_E = (120 + 1) (112 \times 10^{-6})$$

$$I_E = (121) (112 \times 10^{-6})$$

$$I_E = 0.015 \text{ A}$$

$$\text{So, } r_e = \frac{26 \text{ mV}}{0.015 \text{ A}}$$

$$r_e = 1.65 \Omega$$

$$b) Z_i = ?$$

$$Z_i = R_B \parallel \beta(r_e + R_E) \rightarrow \textcircled{A}$$

$$\beta(r_e + R_E) = 120 (1.65 + 0.9 \text{ k})$$

$$= 140 (901.65)$$

$$\beta(r_e + R_E) = 140(901.65)$$

$$\beta(r_e + R_E) = 126231 \Omega$$

Put in eq (A)

$$Z_i = 45 k\Omega \parallel 126 k\Omega$$

$$Z_i = \frac{(45 k\Omega)(126 k\Omega)}{(45 + 126) \times 10^3}$$

$$Z_i = 33 k\Omega$$

$$c) Z_o = R_c = 1.7 k\Omega$$

$$d) A_v = \frac{V_o}{V_i}$$

$$A_v = \frac{V_o}{V_i} = \frac{\beta R_c}{126 k\Omega}$$

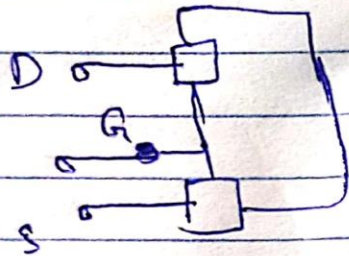
$$A_v = \frac{(140)(1.7 k\Omega)}{126 k\Omega} = \frac{196 k\Omega}{126 k\Omega}$$

$$A_v = 1.5555$$

Question No 4

Solution:-

The construction of p-channel MOSFET is

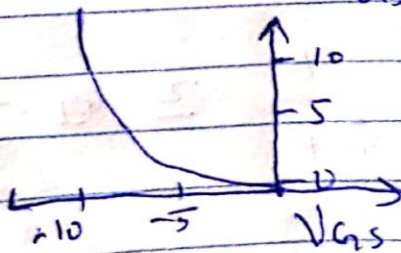


Whenever V_{GS} is enhanced from threshold level, the free carrier will increase in drain,

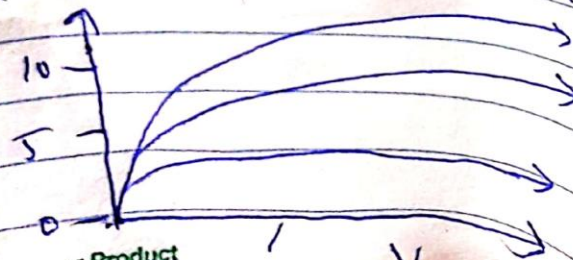
After applying KVL on MOSFET

$$V_{DG} = V_{DS} - V_{GS}$$

And the V_{GS} will be



And the drain characteristic is



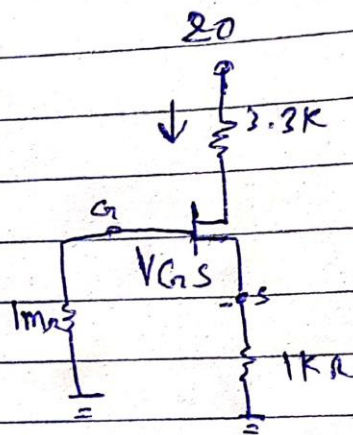
Question No 5

$$V_p (V) = -11 V$$

$$I_{DSS} = 10 \text{ mA}$$

a) $V_{GS} = ?$

$$V_{GS} = -I_D R_S \quad \text{is}$$



the gate to source voltage
So, $I_D = I_{DSS} / 4$

$$V_{GS} = -\left(\frac{10}{4}\right) \text{ mA} (1 \text{ K}\Omega)$$

$$V_{GS} = -(2.5)(1)$$

$$\boxed{V_{GS} = -2.5 \text{ V}}$$

b) $I_{DQ} = 2.5 \text{ V} / 1 \text{ K}\Omega = 2.5 \text{ mA}$

c) $V_{DS} = V_{DD} - I_D (R_S + R_D)$

$$= 20 \text{ V} - (2.5 \text{ mA})(1 \text{ K}\Omega + 3.3 \text{ K}\Omega)$$

$$= 20 \text{ V} - 10.75$$

$$\boxed{V_{DS} = 9.25}$$

d) $V_C = I_D R_S = (2.5 \text{ mA})(1 \text{ K}\Omega)$

$$\boxed{V_C = 2.5 \text{ V}}$$

e) $V_{GQ} = 0 \text{ V}$